



40V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _{D Max} T _A = +25°C
40)/	$33m\Omega$ @ V _{GS} = -10V	-6A
-40V	50mΩ @ V _{GS} = -4.5V	-4.9A

Features

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
 - https://www.diodes.com/quality/product-definitions/
- An automotive-compliant part is available under separate datasheet (DMP4047LFDEQ)

Description and Applications

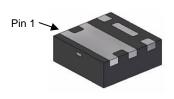
This new generation MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- · General-purpose interfacing switches
- Load switching
- Battery-management applications
- Power-management functions

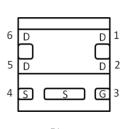
Mechanical Data

- Package: U-DFN2020-6
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0065 grams (Approximate)

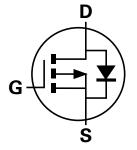
U-DFN2020-6 (Type E)



Bottom View



Pinout Bottom View



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Package	Marking	Reel Size (inches)	Packing		
Part Number	Fackage	Warking	Reel Size (Iliches)	Qty.	Carrier	
DMP4047LFDE-7	U-DFN2020-6 (Type E)	PE	7	3,000	Reel	
DMP4047LFDE-13	U-DFN2020-6 (Type E)	PE	13	10,000	Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

Site 1:



PE = Product Type Marking Code YM = Date Code Marking Y = Year (ex: L = 2024) M = Month (ex: 9 = September)

Date Code Key

Year	2012	-	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	Z	-	L	М	N	Р	R	S	Т	U	V	W
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Site 2 and Site 3:



PE = Product Type Marking Code YWX = Date Code Marking Y or Y = Year (ex: 4 = 2024)

W = Week (ex: a = week 27; z represents week 52 and 53)
X = Internal Code (ex: U = Monday)

2029

2030

2031

2032 2033

Date Code Key

Year

2012

Code	2	-	4	5	6	7	8	9	0	1	2	3
Week	eek 1-26					27	-52		53			
Code		Д	ı-Z			а	-Z			7	<u>z</u>	
Internal Code	Sui	n	Mon		Tue	w	ed	Thu		Fri		Sat
Code	Т		Ш		V	V	V	X		Y		7

2024 2025 2026 2027 2028



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	-40	V		
Gate-Source Voltage			Vgss	±20	V
Ocaliana Basis Ocasa (Nata 5) V	Steady State	T _A = +25°C T _A = +70°C	lo	-3.3 -2.6	А
Continuous Drain Current (Note 5) VGS = -10V	t < 5s	T _A = +25°C T _A = +70°C	ID	-5.3 -4.2	А
Continuous Drain Current (Note 6) Vac. 40V	Steady State	T _A = +25°C T _A = +70°C	I _D	-6.0 -4.8	А
Continuous Drain Current (Note 6) V _{GS} = -10V	t < 5s	T _A = +25°C T _A = +70°C	lo	-9.5 -7.6	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	I _{DM}	-40	Α		
Maximum Body Diode Continuous Current			Is	-3	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	Po	0.7	W
Total Power Dissipation (Note 5)	$T_A = +70$ °C	PD	0.42	VV
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0,JA}	180	°C/W
Thermal Resistance, Junction to Ambient (Note 3)	t < 5s	Keja	76	C/VV
Total Power Dissipation (Note 6)	$T_A = +25$ °C	Pp	2.1	W
Total Fower Dissipation (Note o)	$T_A = +70$ °C	Pυ	1.3	V V
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Rела	58	
Thermal Resistance, Junction to Ambient (Note 6)	t < 5s	Көја	25	°C/W
Thermal Resistance, Junction to Case (Note 6)	$R_{ heta JC}$	10.2		
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

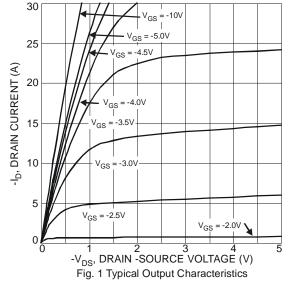
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

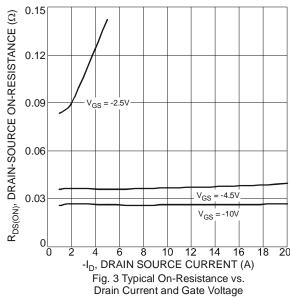
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition			
OFF CHARACTERISTICS (Note 7)									
Drain-Source Breakdown Voltage	BVDSS	-40	_	_	V	V _{GS} = 0V, I _D = -250µA			
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	_		-1	μA	V _{DS} = -40V, V _{GS} = 0V			
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			
ON CHARACTERISTICS (Note 7)									
Gate Threshold Voltage	V _{GS(TH)}	-1.0		-2.2	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$			
Static Drain-Source On-Resistance	D		26	33	mΩ	$V_{GS} = -10V, I_{D} = -4.4A$			
Static Drain-Source On-Resistance	Rds(on)	_	36	50	11122	$V_{GS} = -4.5V$, $I_D = -3.7A$			
Forward Transfer Admittance	Y _{fs}	_	5.2	_	S	V _{DS} = -15V, I _D = -4.4A			
Diode Forward Voltage	V_{SD}	_	-0.75	-1.2	V	$V_{GS} = 0V$, $I_{S} = -3.9A$			
DYNAMIC CHARACTERISTICS (Note 8)									
Input Capacitance	Ciss	_	1382	_	pF	V 00V V 0V			
Output Capacitance	Coss		103		pF	$V_{DS} = -20V, V_{GS} = 0V$ f = 1.0MHz			
Reverse Transfer Capacitance	Crss	_	81	_	pF	T = T.OIVINZ			
Gate Resistance	Rg	_	7.7	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$			
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	11.2	_	nC				
Total Gate Charge (Vgs = -10V)	Qg	_	23.2	_	nC	1,, 20,, 1, 1,0,4			
Gate-Source Charge	Qgs	_	3.3	_	nC	$V_{DS} = -20V, I_{D} = -4.9A$			
Gate-Drain Charge	Q _{gd}	_	3.9	_	nC]			
Turn-On Delay Time	td(on)	_	18.4	_	ns				
Turn-On Rise Time	t _R	_	28.2	_	ns	$V_{DS} = -20V, I_{D} = -3.9A$			
Turn-Off Delay Time	tD(OFF)	_	38.8	_	ns	$V_{GS} = -4.5V$, $R_g = 1\Omega$			
Turn-Off Fall Time	tr	_	28.6	_	ns]			
Reverse-Recovery Time	t _{RR}	_	15.4	_	ns	1 0 0 0 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1			
Reverse-Recovery Charge	Qrr	_	5.4	_	nC	IF = -3.9A, di/dt = 100A/µs			

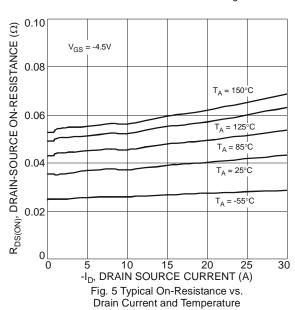
Notes:

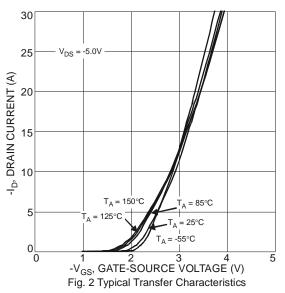
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.











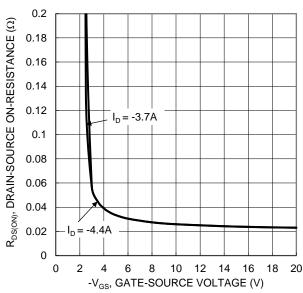
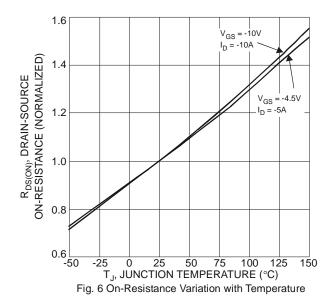
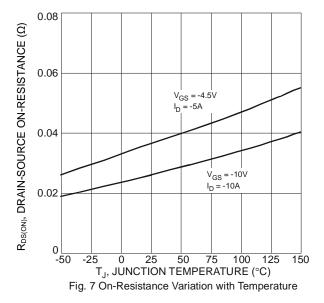
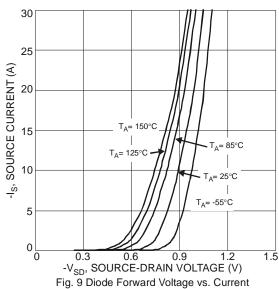


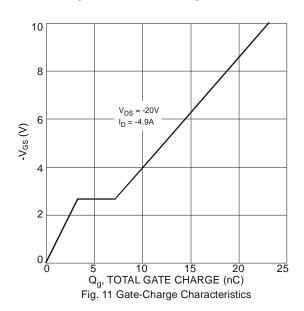
Fig. 4 Typical On-Resistance vs Gate Voltage











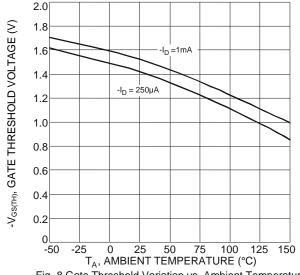
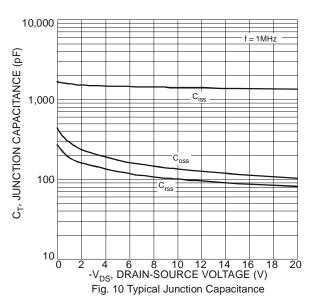
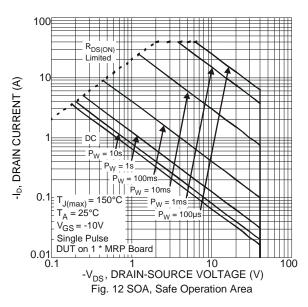
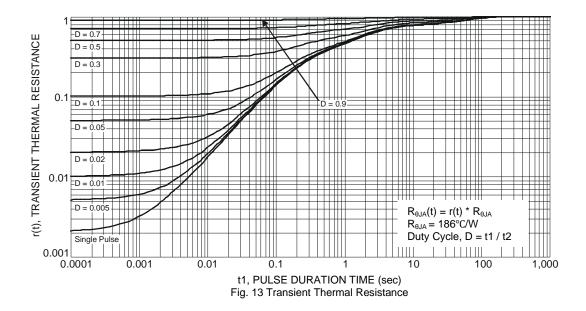


Fig. 8 Gate Threshold Variation vs. Ambient Temperature







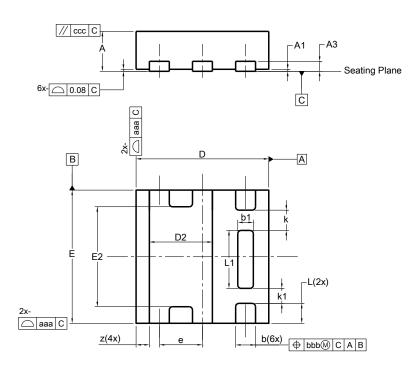




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type E)

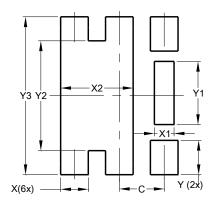


U-DFN2020-6								
(Type E)								
Dim	Min Max Typ							
Α	0.57	0.63	0.60					
A1	0.00	0.05	0.03					
A3	-	0.15						
b	0.25 0.35 0.							
b1	0.185	0.285	0.235					
D	1.95	2.05	2.00					
D2	0.85	1.05	0.95					
Е	1.95	2.05	2.00					
E2	1.40	1.60	1.50					
е	-	-	0.65					
١	0.25	0.35	0.30					
L1	0.82	0.92	0.87					
k	-	-	0.305					
k1	_		0.225					
Z	_	_	0.20					
All	Dimen	sions i	in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type E)



Dimensions	Value (in mm)
С	0.650
Х	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300



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DMP4047LFDE Document number: DS35777 Rev. 8 - 2